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List of Publications by Year in descending order

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50
papers

837
citations

516710

16
h-index

501196

28
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50
all docs

50
docs citations

50
times ranked

1304
citing authors

#	ARTICLE	IF	CITATIONS
1	Raman spectroscopy and field emission characterization of delafossite CuFeO ₂ . Journal of Applied Physics, 2010, 107, .	2.5	89
2	Dielectric anomalies due to grain boundary conduction in chemically substituted BiFeO ₃ . Journal of Applied Physics, 2015, 117, .	2.5	78
3	Structural, electrical, and magnetic properties of chemical solution deposited BiFe _{1-x} Ti _x O ₃ and BiFe _{0.9} Ti _{0.05} Co _{0.05} O ₃ thin films. Journal of Applied Physics, 2009, 106, 014103.	2.5	71
4	Ultrahigh capacitive energy storage in highly oriented Ba(Zr _x Ti _{1-x})O ₃ thin films prepared by pulsed laser deposition. Applied Physics Letters, 2017, 111, .	3.3	51
5	Multilevel unipolar resistive memory switching in amorphous SmGdO ₃ thin film. Applied Physics Letters, 2014, 104, 073501.	3.3	50
6	DyScO ₃ buffer layer for a performing metal-ferroelectric-insulator-semiconductor structure with multiferroic BiFeO ₃ thin film. Applied Physics Letters, 2009, 94, 142907.	3.3	42
7	Structural, electrical, and magnetic properties of chemical solution deposited Bi(Fe _{0.95} Cr _{0.05})O ₃ thin films on platinized silicon substrates. Journal of Applied Physics, 2009, 105, .	2.5	35
8	Ferroelectric photovoltaic properties in doubly substituted (Bi _{0.9} La _{0.1})(Fe _{0.97} Ta _{0.03})O ₃ thin films. Applied Physics Letters, 2015, 106, .	3.3	35
9	Temperature dependent Raman scattering and electronic transitions in rare earth SmFeO ₃ . Ceramics International, 2018, 44, 4198-4203.	4.8	30
10	Freestanding n-Doped Graphene via Intercalation of Calcium and Magnesium into the Buffer Layer of SiC(0001) Interface. Chemistry of Materials, 2020, 32, 6464-6482.	6.7	28
11	A graphene integrated highly transparent resistive switching memory device. APL Materials, 2018, 6, .	5.1	26
12	Unipolar resistive switching in planar Pt/BiFeO ₃ /Pt structure. AIP Advances, 2015, 5, .	1.3	25
13	Structural and Electrical Properties of Lanthanum Gadolinium Oxide: Ceramic and Thin Films for High-k Application. Integrated Ferroelectrics, 2011, 125, 44-52.	0.7	22
14	Dielectric properties and electrical conduction of high-k LaGdO ₃ ceramics. Journal of Applied Physics, 2012, 111, 102811.	2.5	20
15	Nonpolar resistive memory switching with all four possible resistive switching modes in amorphous LaHoO ₃ thin films. Journal of Applied Physics, 2015, 118, .	2.5	18
16	Optical, ferroelectric, and piezoresponse force microscopy studies of pulsed laser deposited Aurivillius Bi ₅ FeTi ₃ O ₁₅ thin films. Journal of Applied Physics, 2014, 116, .	2.5	17
17	Preferential grain growth and improved fatigue endurance in Sr substituted PZT thin films on Pt(111)/TiO _x /SiO ₂ /Si substrates. Journal of Alloys and Compounds, 2009, 482, 253-255.	5.5	16
18	Arrays of Si vacancies in 4H-SiC produced by focused Li ion beam implantation. Scientific Reports, 2021, 11, 3561.	3.3	16

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19	Lanthanum Gadolinium Oxide: A New Electronic Device Material for CMOS Logic and Memory Devices. <i>Materials</i> , 2014, 7, 2669-2696.	2.9	15
20	Optical properties of amorphous high-k LaGdO ₃ films and its band alignment with Si. <i>Journal of Applied Physics</i> , 2012, 111, .	2.5	14
21	Advanced high-k gate dielectric amorphous LaGdO ₃ gated metal-oxide-semiconductor devices with sub-nanometer equivalent oxide thickness. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	13
22	Properties of the new electronic device material La _G O ₃ . <i>Physica Status Solidi (B): Basic Research</i> , 2014, 251, 131-139.	1.5	13
23	Advanced high-k dielectric amorphous LaGdO ₃ based high density metal-insulator-metal capacitors with sub-nanometer capacitance equivalent thickness. <i>Applied Physics Letters</i> , 2013, 102, .	3.3	12
24	On the Resistive Switching and Current Conduction Mechanisms of Amorphous LaGdO ₃ Films Grown by Pulsed Laser Deposition. <i>ECS Transactions</i> , 2013, 53, 229-235.	0.5	10
25	Structural phase transition of ternary dielectric SmGdO ₃ : Evidence from angle dispersive x-ray diffraction and Raman spectroscopic studies. <i>Journal of Applied Physics</i> , 2015, 117, 094101.	2.5	9
26	Holmium hafnate: An emerging electronic device material. <i>Applied Physics Letters</i> , 2015, 106, .	3.3	8
27	Effect of off-center ion substitution in morphotropic lead zirconate titanate composition. <i>Journal of Applied Physics</i> , 2017, 121, 194102.	2.5	8
28	Si:SrTiO ₃ -Al ₂ O ₃ -Si:SrTiO ₃ multi-dielectric architecture for metal-insulator-metal capacitor applications. <i>Applied Physics Letters</i> , 2016, 109, 212901.	3.3	7
29	Metalorganic chemical vapor deposited buffer layer in metalâ€“ferroelectricâ€“insulatorâ€“semiconductor diodes. <i>Solid State Communications</i> , 2009, 149, 2013-2016.	1.9	6
30	Optical Dielectric Function Modeling and Electronic Band Lineup Estimation of Amorphous High-k LaGdO ₃ Films. <i>ECS Journal of Solid State Science and Technology</i> , 2012, 1, N53-N57.	1.8	6
31	Optical properties and electronic band lineup on Si of amorphous zirconium modified Bi ₂ Zn ₂ /3Nb ₄ /3O ₇ thin films. <i>Journal of Alloys and Compounds</i> , 2015, 644, 545-553.	5.5	6
32	Effect of La and Sc co-doping on dielectric and ferroelectric properties of PZT for energy storage capacitors. <i>Journal of Applied Physics</i> , 2021, 130, .	2.5	6
33	Disorder driven structural and dielectric properties of silicon substituted strontium titanate. <i>Journal of Applied Physics</i> , 2015, 118, .	2.5	5
34	The Thermalstability of Voltage Tunability in Pulsed Laser Deposited Ba _{0.6} Sr _{0.4} TiO ₃ Thin Films. <i>Integrated Ferroelectrics</i> , 2015, 166, 140-149.	0.7	5
35	Low-voltage-driven Pt/BiFeO ₃ /DyScO ₃ /p-Si-based metalâ€“ferroelectricâ€“insulatorâ€“semiconductor device for non-volatile memory. <i>Journal of Materials Science</i> , 2018, 53, 4274-4282.	3.7	5
36	Fabrication and Electrical Characterization of High-k LaGdO ₃ Thin Films and Field Effect Transistors. <i>ECS Transactions</i> , 2011, 35, 297-304.	0.5	4

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37	Cauchy-Urbach Dielectric Function Modeling of Amorphous High-k LaGdO ₃ Films. ECS Transactions, 2012, 45, 219-223.	0.5	4
38	Resistive Switching and Current Conduction Mechanisms in Amorphous LaLuO ₃ Thin Films Grown by Pulsed Laser Deposition. Integrated Ferroelectrics, 2014, 157, 47-56.	0.7	3
39	Processing of Cavities in SiC Material for Quantum Technologies. Materials Science Forum, 2018, 924, 905-908.	0.3	3
40	On the doping concentration dependence and dopant selectivity of photogenerated carrier assisted etching of 4H-SiC epilayers. Electrochimica Acta, 2019, 323, 134778.	5.2	3
41	Temperature-Dependent Structural Disintegration of Delafossite CuFeO ₂ . Materials Research Society Symposia Proceedings, 2009, 1183, 55.	0.1	1
42	Unipolar resistive switching behavior of high-k ternary rare-earth oxide LaHoO ₃ thin films for non-volatile memory applications. Materials Research Society Symposia Proceedings, 2015, 1729, 23-28.	0.1	1
43	Analyses of Substrate-Dependent Broadband Microwave (1-40 GHz) Dielectric Properties of Pulsed Laser Deposited Ba _{0.5} Sr _{0.5} TiO ₃ Films. Crystals, 2021, 11, 852.	2.2	1
44	Nonvolatile Resistive Memory Switching in Amorphous LaGdO ₃ Thin Films. Materials Research Society Symposia Proceedings, 2013, 1562, 1.	0.1	0
45	Analysis of Leakage Currents through PLD Grown Ultrathin a-LaGdO ₃ Based High-k Metal Gate Devices. Materials Research Society Symposia Proceedings, 2013, 1561, 1.	0.1	0
46	Properties of the new electronic device material LaGdO ₃ (Phys. Status Solidi B 1/2014). Physica Status Solidi (B): Basic Research, 2014, 251, n/a-n/a.	1.5	0
47	Impact of Processing on Photoluminescence Properties of 4H-SiC for Potential Qubit Applications. ECS Meeting Abstracts, 2017, . .	0.0	0
48	Dielectric and Ferroelectric Properties of Rare Earth Doped Lead Zirconate Titanate Ceramics. ECS Meeting Abstracts, 2018, . .	0.0	0
49	Effect of Zr Substitution for Ti on BaZr _x Ti _{1-x} O ₃ Thin Films for Energy Storage Applications. ECS Meeting Abstracts, 2018, . .	0.0	0
50	Photoelectrochemical Properties of p- and n- Type 4H-SiC Epilayers: Doping Concentration Dependence and Dopant Selectivity. ECS Meeting Abstracts, 2018, . .	0.0	0